

This listing of claims replaces all prior versions, and listings, of claims in the application:

**In the Claims:**

1. (Currently Amended) A switching circuit device comprising:  
  
a common input terminal;  
  
a first output terminal and a second output terminal;  
  
a first switching element connected to the common input terminal and the first output terminal;  
  
a second switching element connected to the common input terminal and the second output terminal;  
  
a control terminal connected to the first switching element and receiving a control signal for the switching circuit device;  
  
a first connection connecting the control terminal to the second switching element;  
  
a second connection connecting the second switching element to a ground;  
  
a bias element applying a bias voltage to the first switching element; and  
  
a direct current isolation element interrupting direct current between the first switching element and the common input terminal or between the second switching element and the common input terminal.
2. (Original) The switching circuit device of claim 1, wherein the bias voltage is a predetermined constant voltage and is constantly applied to the first switching element.
3. (Currently Amended) The switching circuit device of claim 2, wherein the predetermined constant voltage is positive.
4. (Original) The switching circuit device of claim 1, wherein the direct current isolation element comprises a capacitor.

5. (Original) The switching circuit device of claim 4, wherein the bias element comprises a resistor and a power source.

6. (Original) The switching circuit device of claim 5, wherein the capacitor or the resistor is formed on a substrate on which the first switching element and the second switching element are formed.

7. (Original) A semiconductor switching device comprising:

a first field effect transistor and a second field effect transistor each comprising a source electrode, a gate electrode and a drain electrode which are formed on a channel layer of the respective transistor;

a common input terminal connected to the source electrode or the drain electrode of the first transistor and connected to the source electrode or the drain electrode of the second transistor;

a first output terminal connected to the source electrode or the drain electrode of the first transistor which is not connected to the common input terminal;

a second output terminal connected to the source electrode or the drain electrode of the second transistor which is not connected to the common input terminal;

a control terminal connected to the gate electrode of the first transistor, said control terminal receiving a control signal for the switching device;

a bias element applying a bias voltage to the source electrode or the drain electrode of the first transistor;

a first connection connecting the control terminal to the source electrode or the drain electrode of the second transistor;

a second connection connecting the gate electrode of the second transistor to a ground;  
and

a direct current isolation element interrupting direct current between the first transistor and the common input terminal or between the second transistor element and the common input terminal.

8. (Original) The semiconductor switching device of claim 7, wherein the bias voltage is a predetermined constant voltage and is constantly applied to the source electrode or the drain electrode of the first transistor.

9. (Currently Amended) The semiconductor switching device of claim 7, wherein the predetermined constant voltage is positive.

10. (Original) The semiconductor switching device of claim 7, wherein the direct current isolation element comprises a capacitor.

11. (Original) The semiconductor switching device of claim 7, wherein the gate electrode forms Schottky contact with the channel layer, and wherein the source electrode and the drain electrode form ohmic contact with the channel layer.

12. (Original) The semiconductor switching device of claim 7, wherein the first and second transistors are metal-semiconductor field-effect transistors.

13. (Original) The semiconductor switching device of claim 7, wherein the first and second transistors are formed on a substrate and integrated into one chip, and wherein the bias element and the direct current isolation element are externally connected to the chip.

14. (Original) The semiconductor switching device of claim 7, wherein the bias element comprises a resistor and a power source, and wherein the direct current isolation element comprises a capacitor.

15. (Original) The semiconductor switching device of claim 14, wherein the first and second transistors are formed on a substrate and integrated into one chip, and wherein the capacitor or the resistor is formed on the substrate.